TOSHIBA Transistor Silicon NPN Epitaxial Type

## **TPC6503**

**High-Speed Switching Applications DC-DC Converter Applications Strobe Applications** 

- High DC current gain:  $h_{\rm FE}$  = 400 to 1000 (IC = 0.15 A)
- Low collector-emitter saturation voltage:  $V_{CE (sat)} = 0.12 \text{ V (max)}$
- High-speed switching:  $t_f = 45$  ns (typ.)

### **Absolute Maximum Ratings (Ta = 25°C)**

Characteristic		Symbol	Rating	(Unit )	
Collector-base voltage		V <sub>CBO</sub>	40	*	
Collector-emitter voltage		V <sub>CEX</sub>	30	×	
Collector-emitter voltage		V <sub>CEO</sub>	20	> v	
Emitter-base voltage		V <sub>EBO</sub>	7	V	
Collector current	DC	Ic	1.5	A	
	Pulse	I <sub>CP</sub>	2.5		
Base current		I <sub>B</sub>	150	mA	
Collector power dissipation	DC	P <sub>C</sub> (Note)	0.8	w	
	t = 10 s	PC(NOIC)	1.6		
Junction temperature			150	Ç	
Storage temperature range		Tstg	-55 to 150	°C	

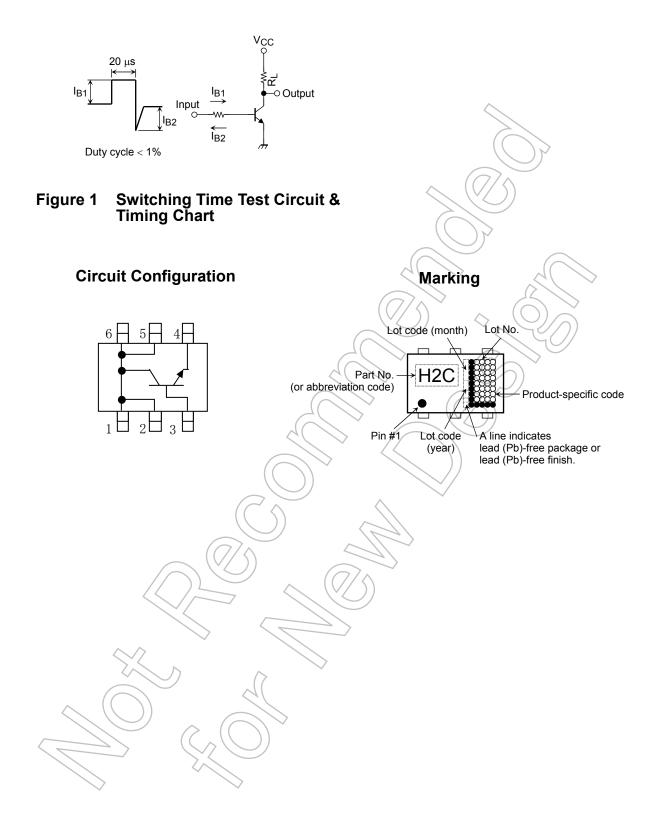
Note: Mounted on FR4 board (glass epoxy, 1.6 mm thick, Cu area: 645 mm<sup>2</sup>)

# Unit: mm **P**0.05 1. Collector 4. Emitter 2. Collector 5. Collector 3. Base 6. Collector **JEDEC** JEITA TOSHIBA 2-3S1A

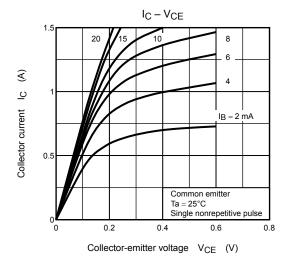
Weight: 0.01 g (typ.)

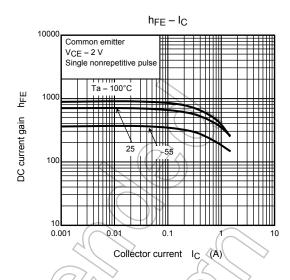
### Electrical Characteristics (Ta = 25°C)

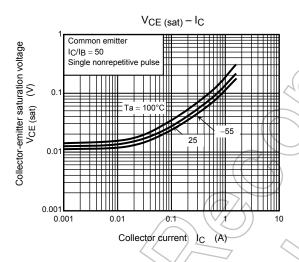
Characteristic		Symbol	Test Conditions	Min	Тур.	Max	Unit	
Collector cut-off current		ICBO	$V_{CB} = 40 \text{ V}, I_{E} = 0$	_	_	100	nA	
Emitter cut-off current		IEBO	V <sub>EB</sub> = 7 V, I <sub>C</sub> = 0	_	_	100	nA	
Collector-emitter breakdown voltage		V (BR) CEO	I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0	20	_	_	V	
DC current gain		h <sub>FE</sub> (1)	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 0.15 A	400	_	1000		
		h <sub>FE</sub> (2)	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 0.5 A	200	_	_		
Collector-emitter saturation voltage		V <sub>CE</sub> (sat)	I <sub>C</sub> = 0.5 A, I <sub>B</sub> = 10 mA	_	_	0.12	V	
Base-emitter saturation voltage		V <sub>BE</sub> (sat)	I <sub>C</sub> = 0.5 A, I <sub>B</sub> = 10 mA	_	_	1.10	V	
Collector output capacitance		C <sub>ob</sub>	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1 MHz	_	18	_	pF	
Switching time	Rise time	t <sub>r</sub>	See Figure 1 circuit diagram.	_	43	_		
	Storage time	t <sub>stg</sub>	$V_{CC} \simeq 12 \text{ V}, R_L = 24 \Omega$	_	295	_	ns	
	Fall time	t <sub>f</sub>	$I_{B1} = -I_{B2} = 17 \text{ mA}$		45			

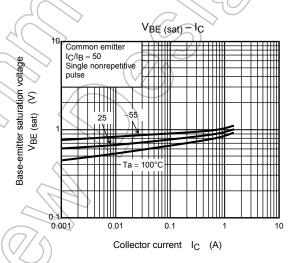


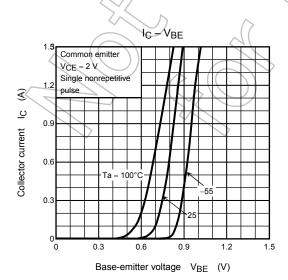
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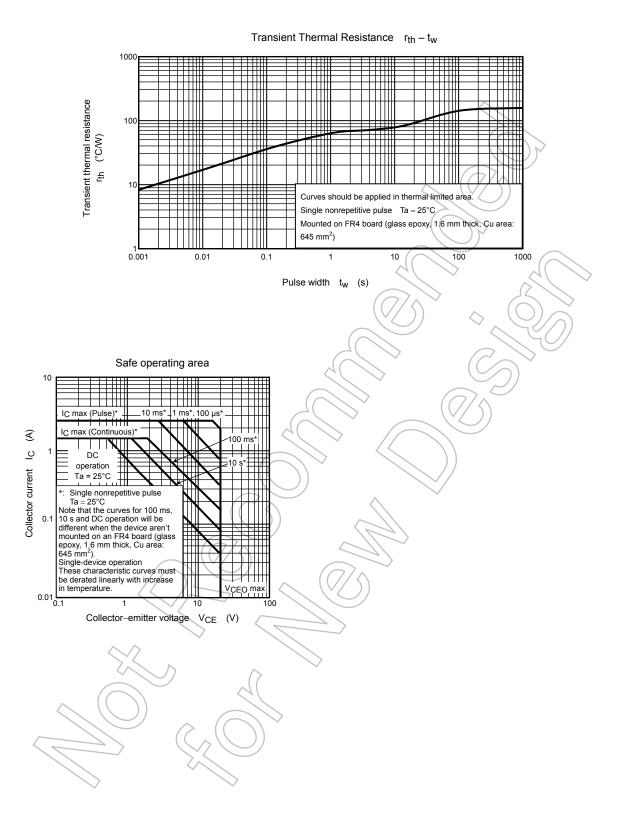








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